

2SJ163

Silicon P-Channel Junction

For general use switching

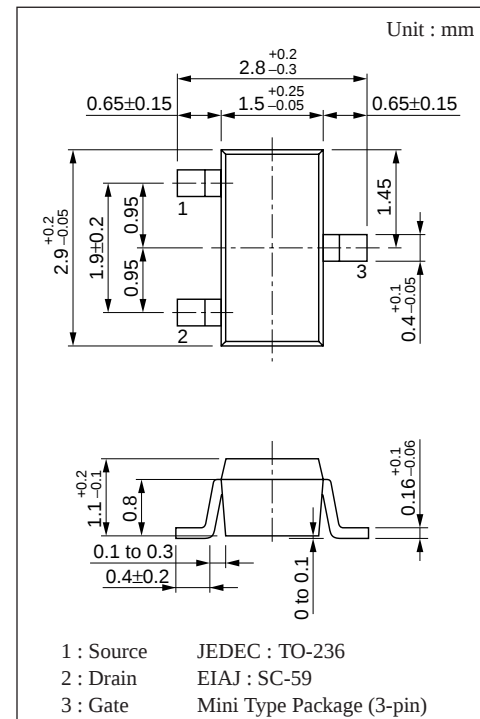
Complementary with 2SK1103

■ Features

- Low ON-resistance
- Low-noise characteristics

■ Absolute Maximum Ratings (Ta = 25°C)

Parameter	Symbol	Rating	Unit
Gate-Drain voltage	V _{GDS}	65	V
Drain current	I _D	−20	mA
Gate current	I _G	−10	mA
Allowable power dissipation	P _D	150	mW
Channel temperature	T _{ch}	150	°C
Storage temperature	T _{stg}	−55 to +150	°C



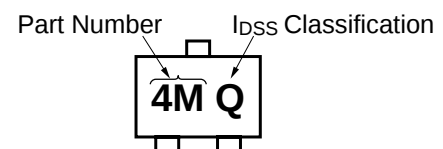
■ Electrical Characteristics (Ta = 25°C)

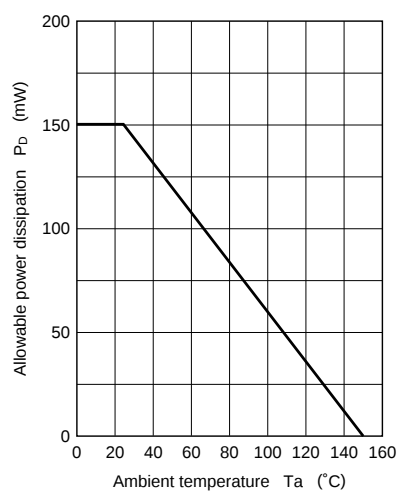
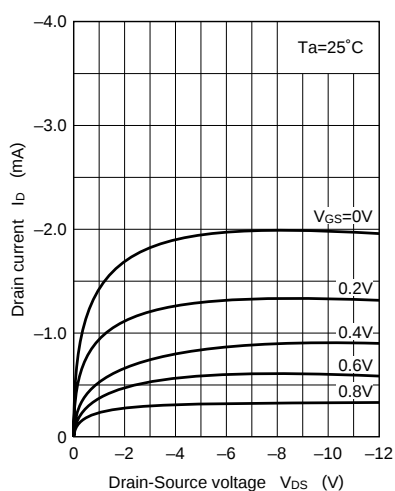
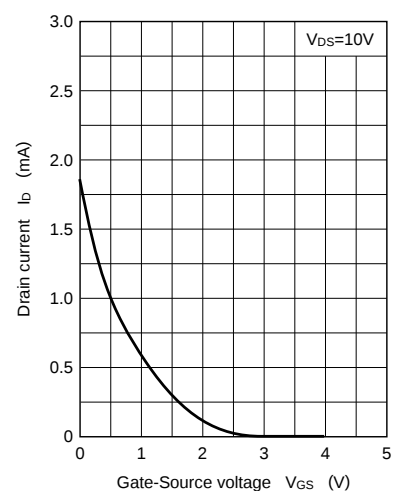
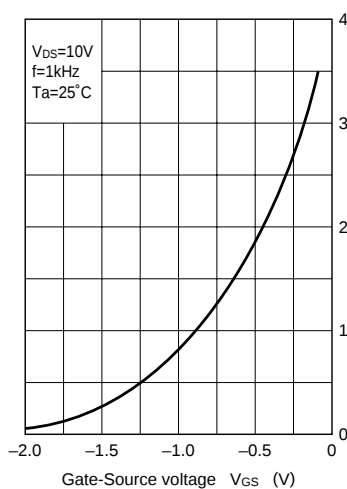
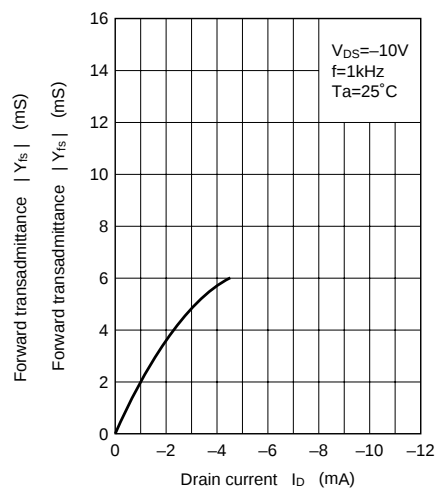
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Drain-Source cut-off current	I _{DSS} *	V _{DS} =−10V, V _{GS} = 0	− 0.2		− 6	mA
Gate-Source leakage current	I _{GSS}	V _{GS} = 30V, V _{DS} = 0			10	nA
Gate-Drain voltage	V _{GDS}	I _G =10μA, V _{DS} = 0	65			V
Gate-Source cut-off voltage	V _{GSC}	V _{DS} = −10V, I _D = −10μA		1.5	3.5	V
Forward transadmittance	Y _{fs}	V _{DS} = −10V, I _D = −1mA, f=1kHz	1.8	2.5		mS
Drain-Source ON-resistance	R _{DS(ON)}	V _{DS} = −10mV, V _{GS} = 0		300		Ω
Input capacitance	C _{iss}	V _{DS} = −10V, V _{GS} = 0, f=1MHz		12		pF
Output capacitance	C _{oss}			4		pF
Feedback capacitance	C _{rss}			4		pF

* I_{DSS} rank classification

Rank	O	P	Q	R
I _{DSS} (mA)	− 0.2 to −1	− 0.6 to −1.5	−1 to − 3	−2.5 to − 6
Part number symbol	4MO	4MP	4MQ	4MR

■ Marking (Example)



$P_D - T_a$  $I_D - V_{DS}$  $I_D - V_{GS}$  $|Y_{fs}| - V_{GS}$  $|Y_{fs}| - I_D$  $C_{iss}, C_{oss}, C_{rss} - V_{DS}$ 